

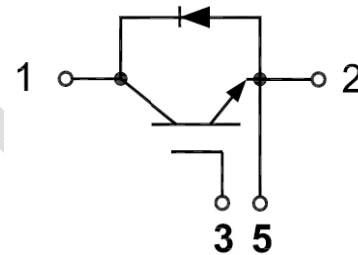
GT900SD120T2ZH-M

IGBT Module

Preliminary Data

Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated > 10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested (2 \times I_c)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Induction Heating
- UPS Systems
- High Power converters

IGBT, Inverter

Maximum Rated Values of IGBT (T_c=25°C unless otherwise specified)

V _{CES}	Collector-Emitter Blocking Voltage		1200	V
V _{GES}	Gate-Emitter Voltage		±20	V
I _c	Continuous Collector Current	T _c =100°C	900	A
		T _c =25°C	1670	A
I _{CM}	Peak Collector Current Repetitive	T _J =175°C	1800	A
t _{SC}	Short Circuit Withstand Time		>10	μs
P _D	Maximum Power Dissipation (IGBT)	T _c =25°C T _{Jmax} =175°C	6000	W

Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)

Static characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	5.0	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 900\text{A}, V_{GE} = 15\text{V}$		1.80	2.00	V
		$T_J = 25^\circ\text{C}$				
		$T_J = 125^\circ\text{C}$		2.10	2.30	V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^\circ\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		55.2		nF
C_{oes}	Output capacitance			3.0		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 900\text{A}, R_G = 2.5\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J = 25^\circ\text{C}$		2250		ns
			$T_J = 125^\circ\text{C}$		1950		
t_r	Rise Time		$T_J = 25^\circ\text{C}$		360		ns
			$T_J = 125^\circ\text{C}$		420		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$		1965		ns
			$T_J = 125^\circ\text{C}$		2100		
t_f	Fall Time		$T_J = 25^\circ\text{C}$		180		ns
			$T_J = 125^\circ\text{C}$		195		
E_{on}	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$		70.2		mJ
			$T_J = 125^\circ\text{C}$		110		
E_{off}	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$		90		mJ	
		$T_J = 125^\circ\text{C}$		128			
Q_g	Total Gate Charge	$T_J = 25^\circ\text{C}$		7470		nC	
RBSOA	Reverse Bias Safe Operation Area	$I_C=1800\text{A}, V_{CC}=1050\text{V}, V_p=1200\text{V}, R_g = 4.7\Omega, V_{GE}=\pm 15\text{V to } 0\text{V}, T_J = 150^\circ\text{C}$	Trapezoid				
SCSOA	Short Circuit Safe Operation Area	$V_{CC} = 600\text{V}, V_{GE} = 15\text{V}, T_J = 150^\circ\text{C}$	10			μs	
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.025		$^\circ\text{C/W}$	

Diode, Inverter

Maximum Rated Values of Diode ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	900	A
I_{FM}	Peak FWD Current Repetitive	1800	A

Electrical Characteristics of Diode ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F = 900\text{A}$	$T_J = 25^\circ\text{C}$	2.2		V
			$T_J = 125^\circ\text{C}$		2.4	
t_{rr}	Reverse Recovery Time		$T_J = 25^\circ\text{C}$	0.41		μs
			$T_J = 125^\circ\text{C}$		0.65	
I_{rr}	Peak Reverse Recovery Current	$I_F = 900\text{A},$ $V_R = 600\text{V},$ $V_{GE} = -15\text{V}$ $diF/dt = 3200\text{A}/\mu\text{s} (T_J = 150^\circ\text{C}),$	$T_J = 25^\circ\text{C}$	286		A
			$T_J = 125^\circ\text{C}$		354	
Q_{rr}	Reverse Recovery Charge		$T_J = 25^\circ\text{C}$	62		μC
			$T_J = 125^\circ\text{C}$		115	
E_{rec}	Reverse Recovery Energy		$T_J = 25^\circ\text{C}$	26		mJ
			$T_J = 125^\circ\text{C}$		46	
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			0.043		$^\circ\text{C}/\text{W}$

Module

Symbol	Description	Min	Typ	Max	Unit
V _{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f = 50Hz, 1minute	2.5		kV
L _{sCE}	Stray Inductance Module		16		nH
T _J	Maximum Junction Temperature			175	°C
T _{JOP}	Maximum Operating Junction Temperature Range	-40		+150	°C
T _{stg}	Storage Temperature	-40		+125	°C
CTI	Comparative Tracking Index	200			
R _{θCS}	Case-To-Sink Thermally (Conductive Grease Applied)		0.03		°C/W
T	Signal Terminals Screw:M4	1.0		2.0	N·m
	Power Terminals Screw:M6	3.0		5.0	N·m
T	Mounting Screw:M6	4.0		6.0	N·m
G	Weight		320		g

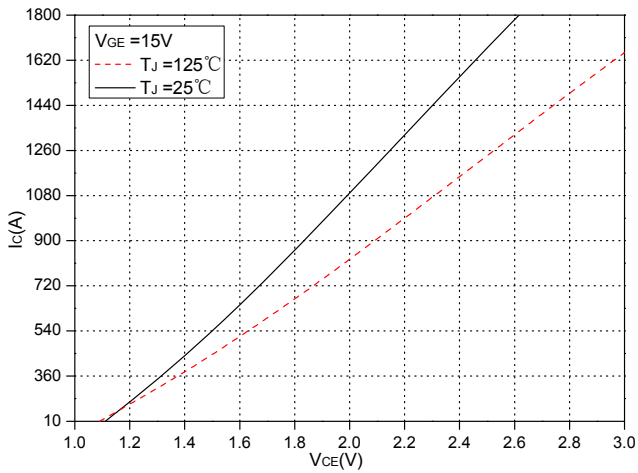


Fig.1 Typical Saturation Voltage Characteristics

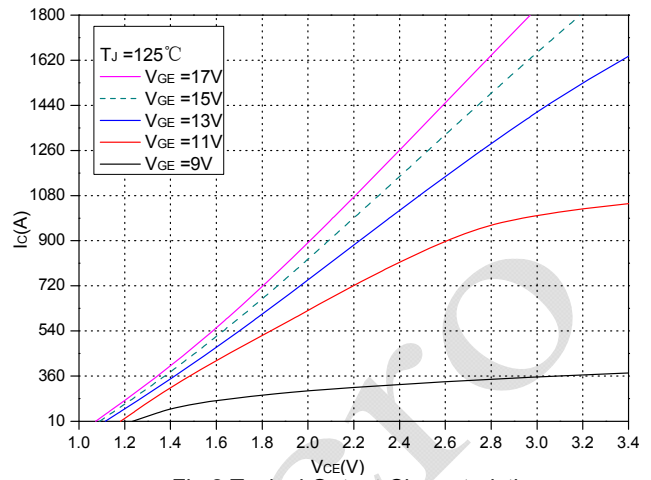


Fig.2 Typical Output Characteristics

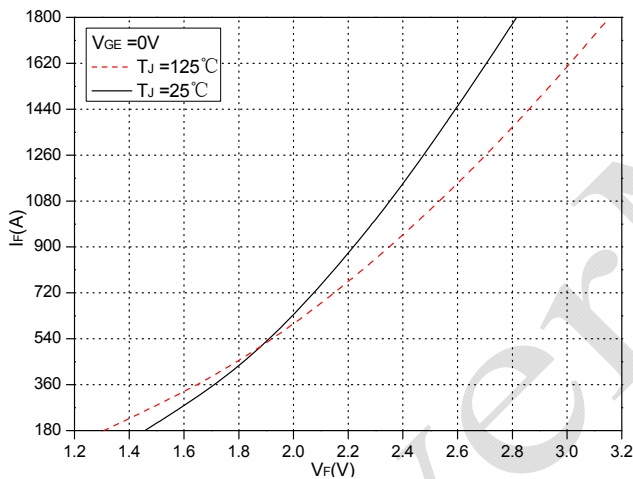


Fig.3 Forward Characteristics of FWD

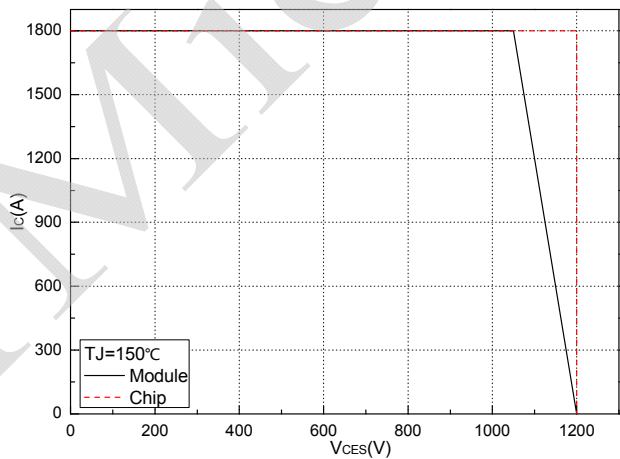


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

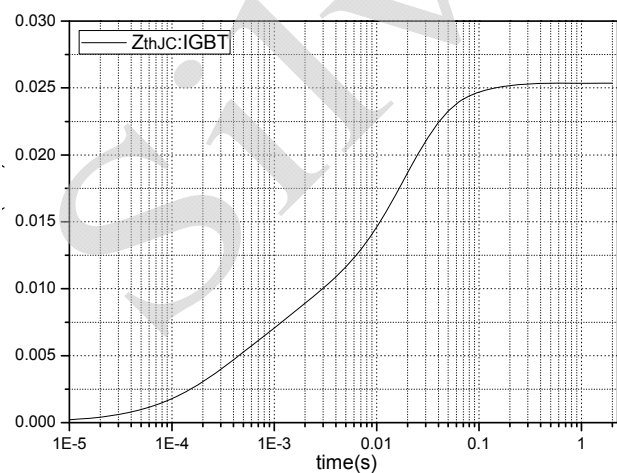


Fig.5 Transient Thermal Impedance (IGBT)

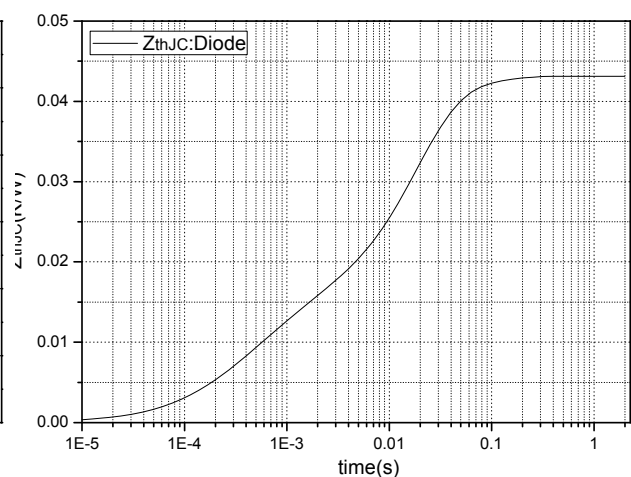
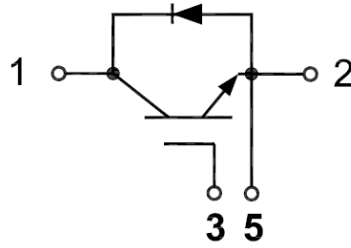
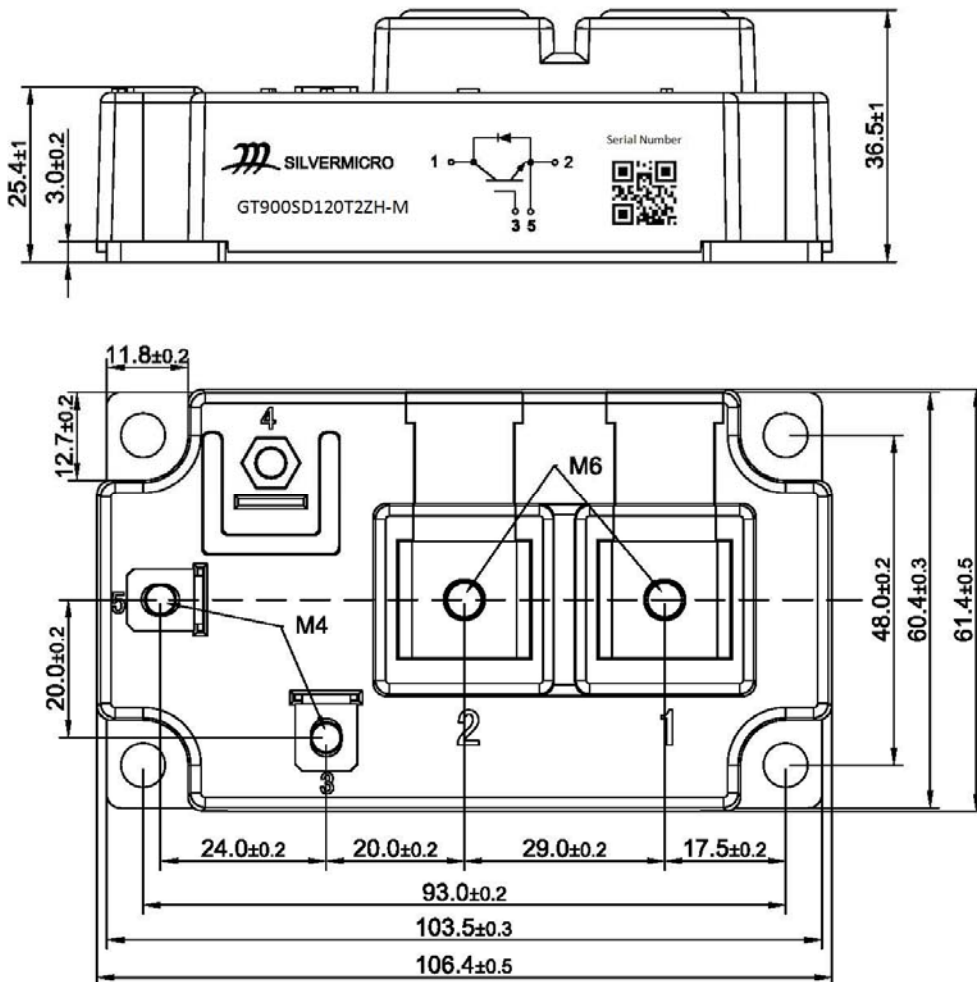


Fig.6 Transient Thermal Impedance (Diode)

Internal Circuit



Package Outline (Unit: mm):





Revision History

Date	Revision	Notes
05/29/2020	01	Initial Release

Announcement

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